

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **B40-28** is Designed for High Reliability Class C Power Amplifier Applications up to 250 MHz.

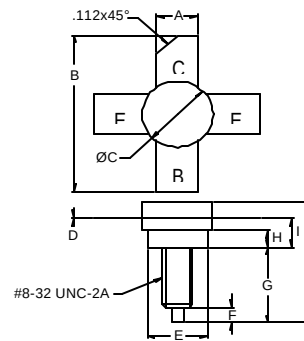
FEATURES:

- $P_G = 8.2$ dB min. at 40 W /175 MHz
- $h_C = 60$ % min. at 40 W /175 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	5.0 A
V_{CBO}	65 V
V_{CEO}	35 V
V_{EBO}	4.0 V
P_{DISS}	60 W
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JA}	2.9 °C/W

PACKAGE STYLE .380 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

ORDER CODE: ASI10859

CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 200$ mA	35			V
BV_{CES}	$I_C = 200$ mA	65			V
BV_{CBO}	$I_C = 10$ mA	65			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CES}	$V_{CE} = 30$ V			10	mA
I_{CBO}	$V_{CB} = 30$ V			1.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 500$ mA	5.0		200	---
C_{ob}	$V_{CB} = 30$ V $f = 1.0$ MHz			65	pF
P_G	$V_{CE} = 28$ V $P_{OUT} = 40$ W $f = 175$ MHz	8.2			dB
h_C		60			%



ADVANCED SEMICONDUCTOR, INC.

7525 ETHEL AVENUE • NORTH HOLLYWOOD, CA 91605 • (818) 982-1202 • TELEX: 18-2651 • FAX (818) 765-3004